



8ETH06
8ETH06S
8ETH06-1

Hyperfast Rectifier

Features

- Hyperfast Recovery Time
- Low Forward Voltage Drop
- Low Leakage Current
- 175°C Operating Junction Temperature

$t_{rr} = 30\text{ns}$
 $I_{F(AV)} = 8\text{Amp}$
 $V_R = 600\text{V}$

Description/ Applications

State of the art Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, Hyperfast recover time, and soft recovery.
The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.
These devices are intended for use in PFC Boost stage in the AC-DC section of SMPS, inverters or as freewheeling diodes.
The IR extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

Absolute Maximum Ratings

Parameters		Max	Units
V_{RRM}	Peak Repetitive Peak Reverse Voltage	600	V
$I_{F(AV)}$	Average Rectified Forward Current	8	A
I_{FSM}	Non Repetitive Peak Surge Current	120	
I_{FM}	Peak Repetitive Forward Current	16	
T_J, T_{STG}	Operating Junction and Storage Temperatures	- 65 to 175	°C

Case Styles		
8ETH06  TO-220AC	8ETH06S  D ² PAK	8ETH06-1  TO-262

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters	Min	Typ	Max	Units	Test Conditions
V_{BR}, V_r Breakdown Voltage, Blocking Voltage	600	-	-	V	$I_R = 100\mu\text{A}$
V_F Forward Voltage	-	-	2.1	V	$I_F = 8\text{A}, T_J = 25^\circ\text{C}$
	-	-	1.7	V	$I_F = 8\text{A}, T_J = 150^\circ\text{C}$
I_R Reverse Leakage Current	-	-	100	μA	$V_R = V_R \text{ Rated}$
	-	-	500	μA	$T_J = 150^\circ\text{C}, V_R = V_R \text{ Rated}$
C_T Junction Capacitance	-	-	-	pF	$V_R = 600\text{V}$
L_S Series Inductance	-	-	-	nH	Measured lead to lead 5mm from package body

Dynamic Recovery Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Parameters	Min	Typ	Max	Units	Test Conditions
t_{rr} Reverse Recovery Time	-	25	30	ns	$I_F = 1.0\text{A}, di_F/dt = 50\text{A}/\mu\text{s}, V_R = 30\text{V}$
	-	27	35		$I_F = 8\text{A}, di_F/dt = 200\text{A}/\mu\text{s}, V_R = 200\text{V}$
	-	-	-		$T_J = 25^\circ\text{C}$
	-	-	-		$T_J = 125^\circ\text{C}$
I_{RRM} Peak Recovery Current	-	2	-	A	$T_J = 25^\circ\text{C}$
	-	-	-		$T_J = 125^\circ\text{C}$
Q_{rr} Reverse Recovery Charge	-	25	56	nC	$T_J = 25^\circ\text{C}$
	-	-	-		$T_J = 125^\circ\text{C}$

Thermal - Mechanical Characteristics

Parameters	Min	Typ	Max	Units
T_J Max. Junction Temperature Range	-	-	-65 to 175	$^\circ\text{C}$
T_{Stg} Max. Storage Temperature Range	-	-	-65 to 175	
R_{thJC} Thermal Resistance, Junction to Case Per Leg	-	1.2	2	$^\circ\text{C}/\text{W}$
R_{thJA} ① Thermal Resistance, Junction to Ambient Per Leg	-	-	-	
R_{thCS} ② Thermal Resistance, Case to Heatsink	-	0.5	-	
Weight	-	2.0	-	g
	-	0.07	-	(oz)
Mounting Torque	6.0	-	12	Kg-cm
	5.0	-	10	lbf.in

① Typical Socket Mount

② Mounting Surface, Flat, Smooth and Greased